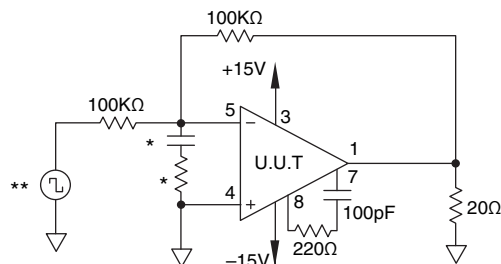


SG	PARAMETER	SYMBOL	TEMP.	POWER	TEST CONDITIONS	MIN	MAX	UNITS
1	Quiescent Current	I_Q	25°C	±35V	$V_{IN} = 0, A_V = 100$		85	mA
1	Input Offset Voltage	V_{OS}	25°C	±35V	$V_{IN} = 0, A_V = 100$		3	mV
1	Input Offset Voltage	V_{OS}	25°C	±12V	$V_{IN} = 0, A_V = 100$		5.3	mV
1	Input Offset Voltage	V_{OS}	25°C	±40V	$V_{IN} = 0, A_V = 100$		3.5	mV
1	Input Bias Current, +IN	$+I_B$	25°C	±35V	$V_{IN} = 0$		100	pA
1	Input Bias Current, -IN	$-I_B$	25°C	±35V	$V_{IN} = 0$		100	pA
1	Input Offset Current	I_{OS}	25°C	±35V	$V_{IN} = 0$		50	pA
3	Quiescent Current	I_Q	-55°C	±35V	$V_{IN} = 0, A_V = 100$		165	mA
3	Input Offset Voltage	V_{OS}	-55°C	±35V	$V_{IN} = 0, A_V = 100$		5.4	mV
3	Input Offset Voltage	V_{OS}	-55°C	±12V	$V_{IN} = 0, A_V = 100$		7.7	mV
3	Input Offset Voltage	V_{OS}	-55°C	±40V	$V_{IN} = 0, A_V = 100$		5.9	mV
3	Input Bias Current, +IN	$+I_B$	-55°C	±35V	$V_{IN} = 0$		100	pA
3	Input Bias Current, -IN	$-I_B$	-55°C	±35V	$V_{IN} = 0$		100	pA
3	Input Offset Current	I_{OS}	-55°C	±35V	$V_{IN} = 0$		50	pA
2	Quiescent Current	I_Q	125°C	±35V	$V_{IN} = 0, A_V = 100$		140	mA
2	Input Offset Voltage	V_{OS}	125°C	±35V	$V_{IN} = 0, A_V = 100$		6	mV
2	Input Offset Voltage	V_{OS}	125°C	±12V	$V_{IN} = 0, A_V = 100$		8.3	mV
2	Input Offset Voltage	V_{OS}	125°C	±40V	$V_{IN} = 0, A_V = 100$		6.5	mV
2	Input Bias Current, +IN	$+I_B$	125°C	±35V	$V_{IN} = 0$		10	nA
2	Input Bias Current, -IN	$-I_B$	125°C	±35V	$V_{IN} = 0$		10	nA
2	Input Offset Current	I_{OS}	125°C	±35V	$V_{IN} = 0$		10	nA
4	Output Voltage, $I_O = 3A$	V_O	25°C	±21.3V	$R_L = 3.75\Omega$	11.3		V
4	Output Voltage, $I_O = 66mA$	V_O	25°C	±40V	$R_L = 500\Omega$	33		V
4	Output Voltage, $I_O = 2A$	V_O	25°C	±38V	$R_L = 15\Omega$	30		V
4	Current Limits	I_{CL}	25°C	±32.2V	$R_L = 3.75\Omega$	3.4	6	A
4	Stability/Noise	E_N	25°C	±35V	$R_L = 500\Omega, A_V = 1, C_L = 1.5nF$		1	mV
4	Slew Rate	SR	25°C	±35V	$R_L = 500\Omega$	25	500	V/μs
4	Open Loop Gain	A_{OL}	25°C	±35V	$R_L = 500\Omega, F = 10Hz$	80		dB
4	Common Mode Rejection	CMR	25°C	±34.5V	$R_L = 500\Omega, F = DC, V_{CM} = \pm 22.5V$	64		dB
6	Output Voltage, $I_O = 3A$	V_O	-55°C	±21.3V	$R_L = 3.75\Omega$	11.3		V
6	Output Voltage, $I_O = 66mA$	V_O	-55°C	±40V	$R_L = 500\Omega$	33		V
6	Output Voltage, $I_O = 2A$	V_O	-55°C	±38V	$R_L = 15\Omega$	30		V
6	Stability/Noise	E_N	-55°C	±35V	$R_L = 500\Omega, A_V = 1, C_L = 1.5nF$		1	mV
6	Slew Rate	SR	-55°C	±35V	$R_L = 500\Omega$	25	500	V/μs
6	Open Loop Gain	A_{OL}	-55°C	±35V	$R_L = 500\Omega, F = 10Hz$	80		dB
6	Common Mode Rejection	CMR	-55°C	±34.5V	$R_L = 500\Omega, F = DC, V_{CM} = \pm 22.5V$	64		dB
5	Output Voltage, $I_O = 66mA$	V_O	125°C	±40V	$R_L = 500\Omega$	33		V
5	Output Voltage, $I_O = 1A$	V_O	125°C	±23.5V	$R_L = 15\Omega$	15		V
5	Stability/Noise	E_N	125°C	±35V	$R_L = 500\Omega, A_V = 1, C_L = 1.5nF$		1	mV
5	Slew Rate	SR	125°C	±35V	$R_L = 500\Omega$	20	500	V/μs
5	Open Loop Gain	A_{OL}	125°C	±35V	$R_L = 500\Omega, F = 10Hz$	80		dB
5	Common Mode Rejection	CMR	125°C	±34.5V	$R_L = 500\Omega, F = DC, V_{CM} = \pm 22.5V$	64		dB

BURN IN CIRCUIT



* These components are used to stabilize device due to poor high frequency characteristics of burn in board.

** Input signals are calculated to result in internal power dissipation of approximately 2.1W at case temperature = 125°C.